

Dual N-Channel MOSFET

General Description

The WSP9926A is the highest performance trench N-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WSP9926A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

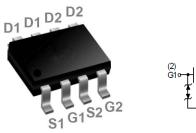
Product Summery

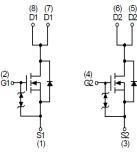
BVDSS	RDSON	ID		
20V	20mΩ	7.5A		

Applications

- High Frequency Point-of-Load Synchronous
 Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- ESD:2KV

SOP-8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	20	V	
V_{GS}	Gate-Source Voltage	±12	V	
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	7.5	А	
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	6.0	А	
I _{DM}	Pulsed Drain Current ²	30	Α	
P _D @T _A =25°C	Total Power Dissipation ³	2	W	
T _{STG}	Storage Temperature Range -55 to 150		°C	
T _J	Operating Junction Temperature Range -55 to 150		$^{\circ}$ C	

Thermal Data

Symbol	Parameter Ty		Max.	Unit	
$R_{ heta JA}$	Thermal Resistance Junction-ambient ¹		62.5	°C/W	
R _{0JC}	Thermal Resistance Junction-Case ¹		10	°C/W	



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I _D =1mA		0.022		V/°C
D	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =7.5A		20	25	mΩ
R _{DS(ON)}		V _{GS} =2.5V , I _D =5.5A		25	35	
$V_{GS(th)}$	Gate Threshold Voltage	V V I 050 A	0.5	0.7	1.1	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-2.33		mV/℃
	Danier Course I and and Course	V_{DS} =16V , V_{GS} =0V , T_J =25 $^{\circ}\mathrm{C}$			1	- uA
I _{DSS}	Drain-Source Leakage Current	V_{DS} =16V , V_{GS} =0V , T_J =55 $^{\circ}\mathrm{C}$			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm12V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =5A		25		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		4.5		Ω
Q_g	Total Gate Charge (4.5V)	V _{DS} =10V , V _{GS} =4.5V , I _D =7.5A		10.3	15	
Q_{gs}	Gate-Source Charge			2.4		nC
$Q_{\sf gd}$	Gate-Drain Charge			3.2		
$T_{d(on)}$	Turn-On Delay Time	V_{DD} =10V , V_{GS} =4.5V , R_{G} =6 Ω I_{D} =5A , R_{L} =10 Ω .		4.2	9.1	
T _r	Rise Time			11.2	20	no
T _{d(off)}	Turn-Off Delay Time			38.5	70	ns
T _f	Fall Time			20.5	35	
C _{iss}	Input Capacitance	V _{DS} =10V , V _{GS} =0V , f=1MHz		620		
C _{oss}	Output Capacitance			110		pF
C _{rss}	Reverse Transfer Capacitance			115		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	// =// =0// Force Current			1	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			30	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1.3	V
t _{rr}	Reverse Recovery Time			19.2		nS
Q _{rr}	Reverse Recovery Charge	lF=8A , dl/dt=100A/μs , T _J =25℃		4.6		nC

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

 $[\]textbf{4.The data is theoretically the same as } I_{D} \text{ and } I_{DM} \text{ , in real applications , should be limited by total power dissipation.}$



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Typical Characteristics

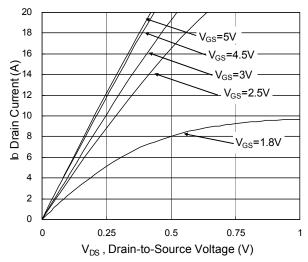


Fig.1 Typical Output Characteristics

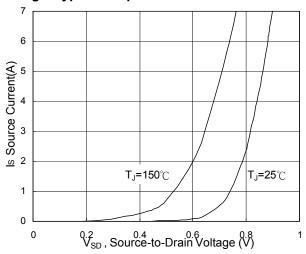


Fig.3 Forward Characteristics Of Reverse

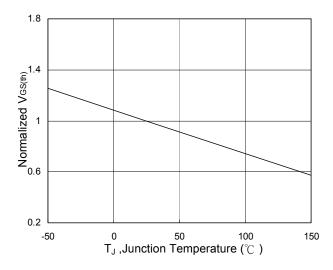


Fig.5 Normalized V_{GS(th)} vs. T_J

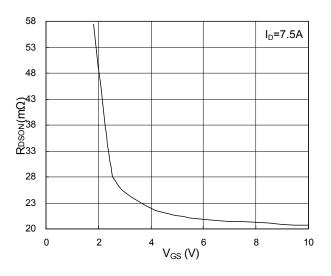


Fig.2 On-Resistance vs. Gate-Source

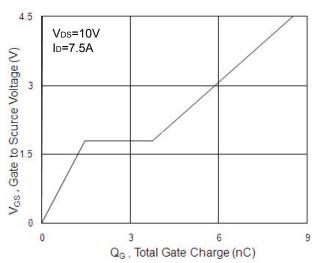


Fig.4 Gate-Charge Characteristics

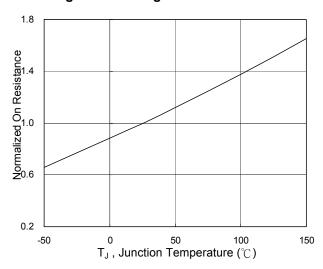
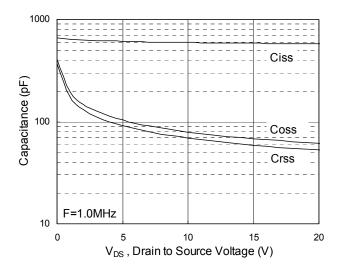


Fig.6 Normalized R_{DSON} vs. T_J







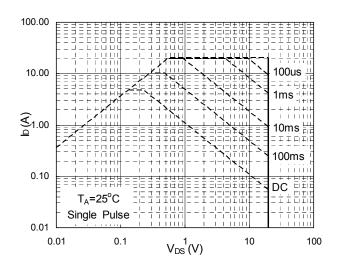


Fig.7 Capacitance

Fig.8 Safe Operating Area

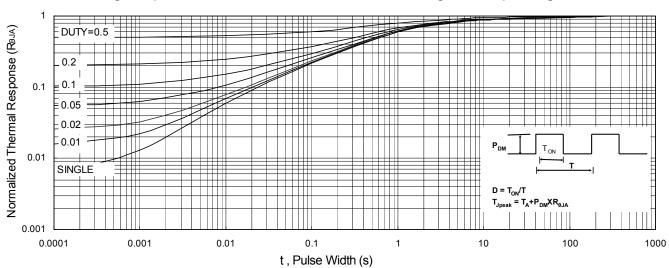


Fig.9 Normalized Maximum Transient Thermal Impedance

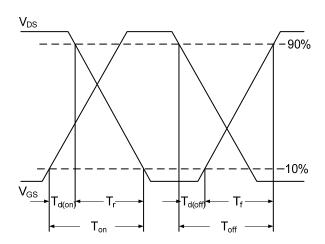


Fig.10 Switching Time Waveform

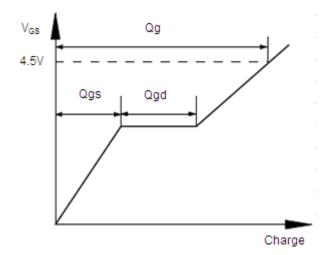


Fig.11 Gate Charge Waveform



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